In the Claims:

1. (currently amended) A method of processing a surface of a nitride semiconductor crystal, wherein

a surface of a nitride semiconductor crystal [[~~(11)~~]] is brought into contact with a liquid containing at least Na, Li or Ca as a processing ~~solution (15).~~ solution.

2. (currently amended) The method of processing a surface of a nitride semiconductor crystal according to claim 1, wherein

said processing solution [[~~(15)~~]] is a liquid containing at least Na and has an Na content of 5-95 mol%.

3. (currently amended)The method of processing a surface of a nitride semiconductor crystal according to claim 1, wherein

said processing solution [[~~(15)~~]] is a liquid containing at least Li and has an Li content of 5-100 mol%.

4. (currently amended) The method of processing a surface of a nitride semiconductor crystal according to claim 1, wherein

said nitride semiconductor crystal [[~~(11)~~]] is an $Al_xGa_yIn_{1-x-y}N$ semiconductor crystal ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$).

5. (currently amended) A nitride semiconductor crystal having a maximum depth of a surface scratch of at most 0.01 μm and obtained with a method of processing a surface of a nitride semiconductor crystal wherein a surface of a nitride semiconductor crystal [[~~(11)~~]] is brought into contact with a liquid containing at least Na, Li or Ca as a processing ~~solution (15).~~ solution.

6. (currently amended) The nitride semiconductor crystal according to claim 5, wherein

said processing solution [[~~(15)~~]] is a liquid containing at least Na and has an Na content of 5-95 mol%.

7. (currently amended) The nitride semiconductor crystal according to claim 5, wherein

said processing solution [[~~(15)~~]] is a liquid containing at least Li and has an Li content of 5-100 mol%.

8. (currently amended) The nitride semiconductor crystal according to claim 5, wherein

said nitride semiconductor crystal [[~~(11)~~]] is an $Al_xGa_yIn_{1-x-y}N$ semiconductor crystal ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$).

9. (currently amended) A nitride semiconductor crystal having an average thickness of a damaged layer of at most 2 μm and

obtained with a method of processing a surface of a nitride semiconductor crystal wherein a surface of a nitride semiconductor crystal [[~~(11)~~]] is brought into contact with a liquid containing at least Na, Li or Ca as a processing ~~solution (15).~~ solution.

10. (currently amended) The nitride semiconductor crystal according to claim 9, wherein

said processing solution [[~~(15)~~]] is a liquid containing at least Na and has an Na content of 5-95 mol%.

11. (currently amended) The nitride semiconductor crystal according to claim 9, wherein

said processing solution [[~~(15)~~]] is a liquid containing at least Li and has an Li content of 5-100 mol%.

12. (currently amended) The nitride semiconductor crystal according to claim 9, wherein

said nitride semiconductor crystal [[~~(11)~~]] is an $Al_xGa_yIn_{1-x-y}N$ semiconductor crystal ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x+y \leq 1$).

[AMENDMENT CONTINUES ON NEXT PAGE]